

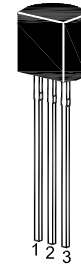
# ST 2SC2668

## NPN Silicon Epitaxial Planar Transistor

High frequency amplifier applications.

The transistor is subdivided into three groups, R, O and Y, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



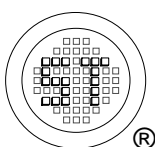
1. Emitter 2. Collector 3. Base  
TO-92 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	40	V
Collector Emitter Voltage	$V_{CEO}$	30	V
Emitter Base Voltage	$V_{EBO}$	4	V
Collector Current	$I_C$	20	mA
Base Current	$I_B$	4	mA
Power Dissipation	$P_{tot}$	100	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $V_{CE} = 6\text{ V}$ , $I_C = 1\text{ mA}$	Current Gain Group R	$h_{FE}$	40	-	80	-
	O	$h_{FE}$	70	-	140	-
	Y	$h_{FE}$	100	-	200	-
Collector Base Cutoff Current at $V_{CB} = 40\text{ V}$	$I_{CBO}$	-	-	500	nA	
Emitter Base Cutoff Current at $V_{EB} = 4\text{ V}$	$I_{EBO}$	-	-	500	nA	
Transition Frequency at $V_{CE} = 6\text{ V}$ , $I_C = 1\text{ mA}$	$f_T$	-	550	-	MHz	
Reverse Transfer Capacitance at $V_{CE} = 6\text{ V}$ , $f = 1\text{ MHz}$	$C_{re}$	-	0.7	-	pF	



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